Lattice Semiconductor Corporation - LFXP2-17E-6FTN256C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	282624
Number of I/O	201
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-17e-6ftn256c

sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

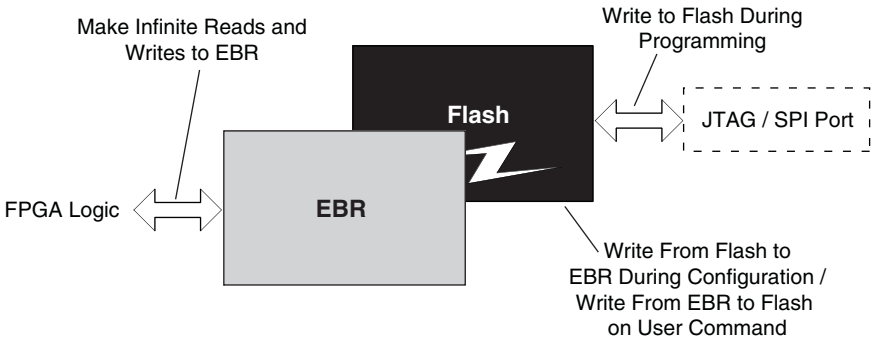
Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

FlashBAK EBR Content Storage

All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.

Figure 2-16. FlashBAK Technology



Memory Cascading

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

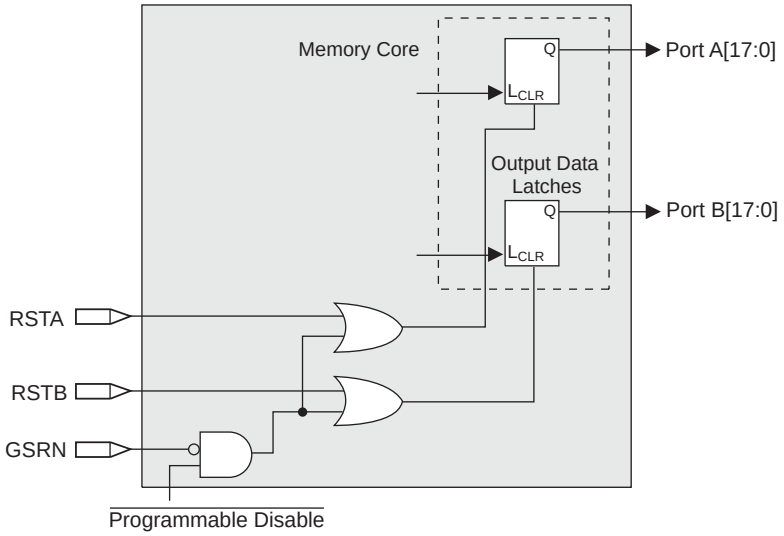
EBR memory supports two forms of write behavior for single port or dual port operation:

1. Normal – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. Write Through – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. GSRN, the global reset signal, resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-17.

Figure 2-17. Memory Core Reset



- In the ‘Signed/Unsigned’ options the operands can be switched between signed and unsigned on every cycle.
- In the ‘Add/Sub’ option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

MULT sysDSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, A and B, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-20 shows the MULT sysDSP element.

Figure 2-20. MULT sysDSP Element

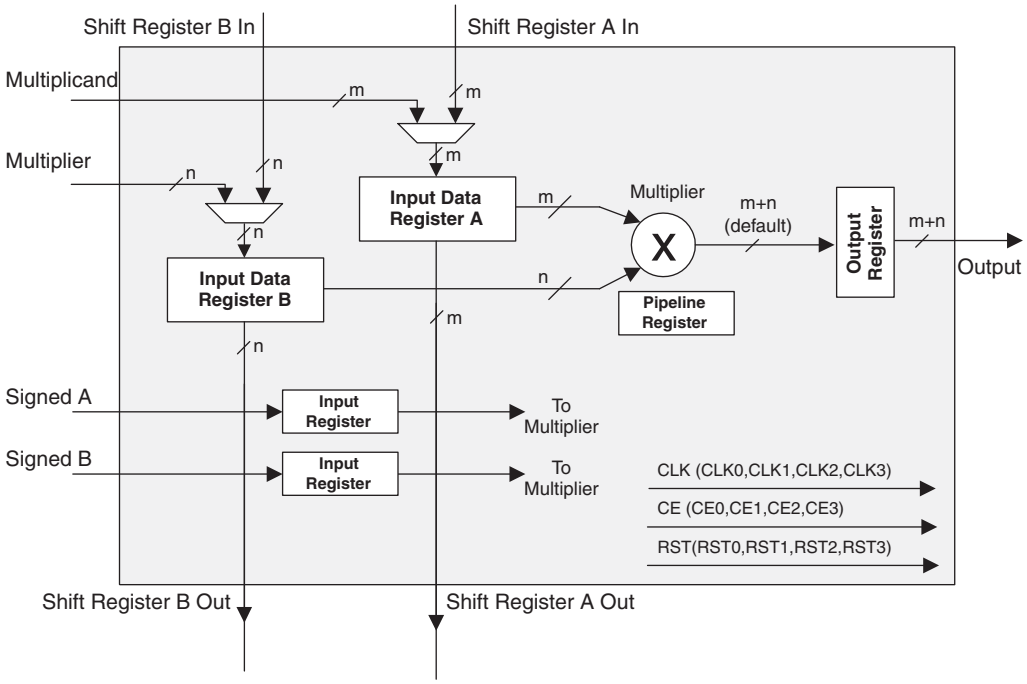


Figure 2-28. DQS Input Routing (Left and Right)

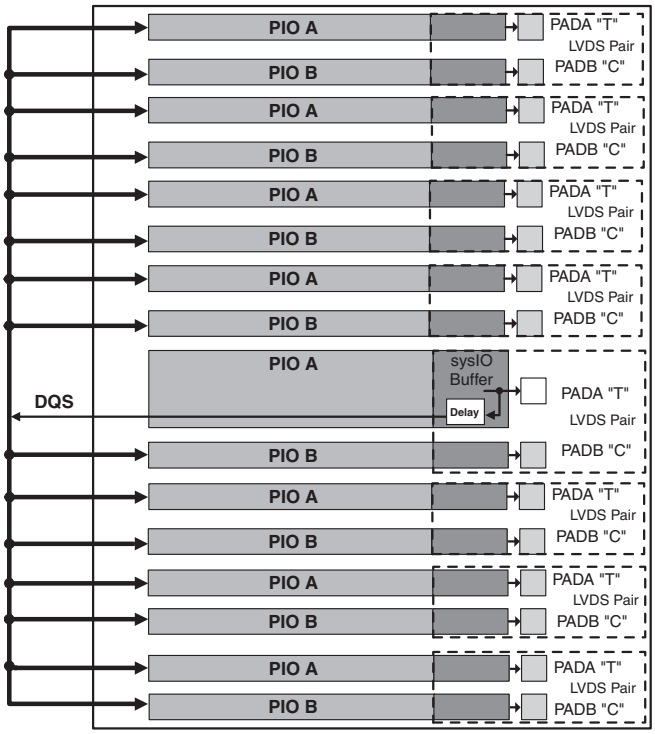
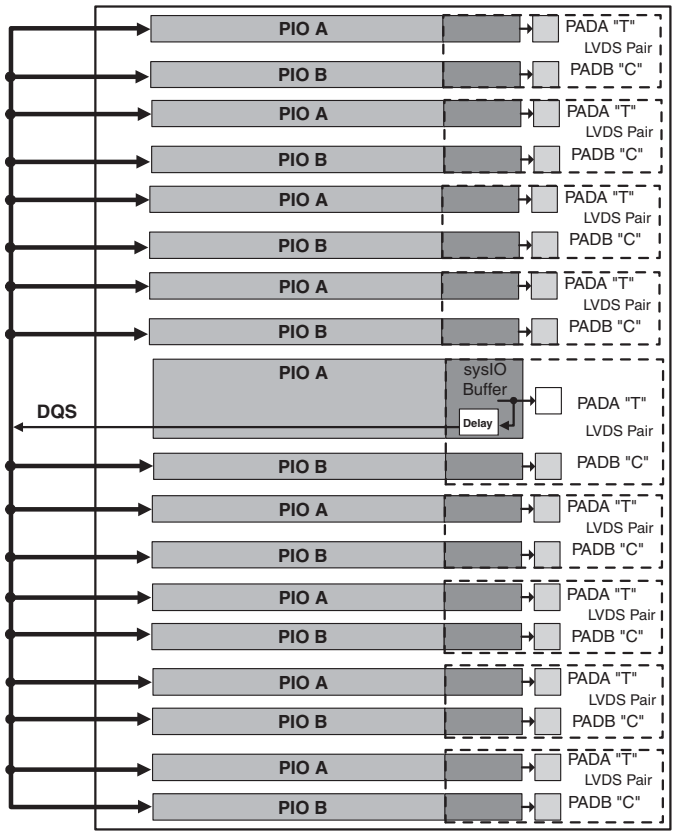


Figure 2-29. DQS Input Routing (Top and Bottom)

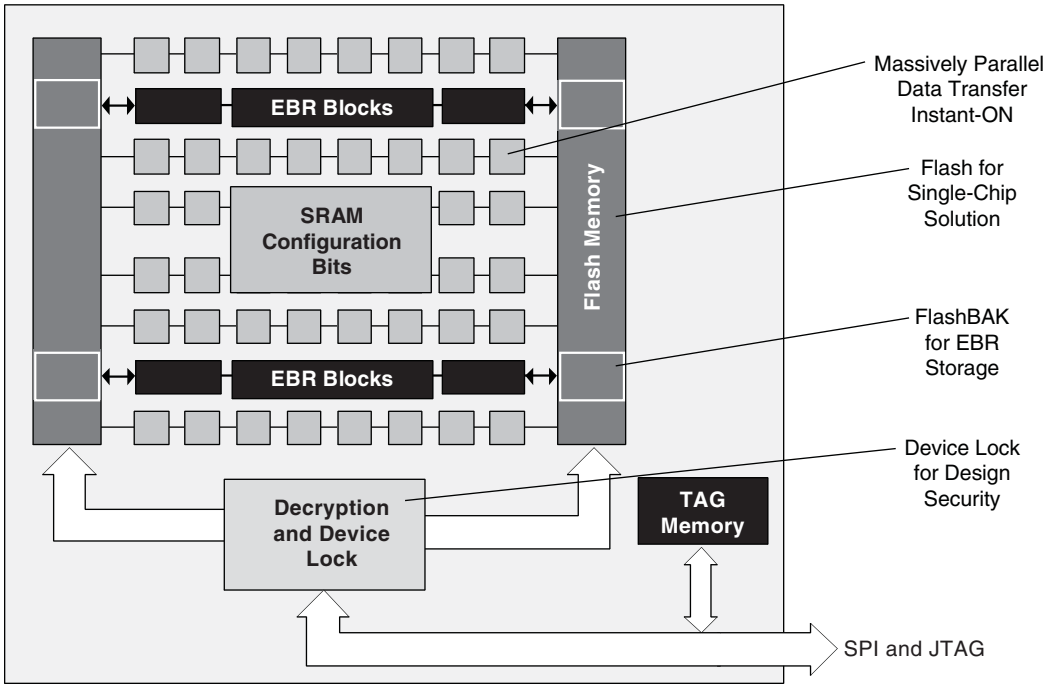


and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port has its own supply voltage V_{CCJ} and can operate with LVCMOS3.3, 2.5, 1.8, 1.5 and 1.2 standards. For more information, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

flexiFLASH Device Configuration

The LatticeXP2 devices combine Flash and SRAM on a single chip to provide users with flexibility in device programming and configuration. Figure 2-33 provides an overview of the arrangement of Flash and SRAM configuration cells within the device. The remainder of this section provides an overview of these capabilities. See TN1141, LatticeXP2 sysCONFIG Usage Guide for a more detailed description.

Figure 2-33. Overview of Flash and SRAM Configuration Cells Within LatticeXP2 Devices



At power-up, or on user command, data is transferred from the on-chip Flash memory to the SRAM configuration cells that control the operation of the device. This is done with massively parallel buses enabling the parts to operate within microseconds of the power supplies reaching valid levels; this capability is referred to as Instant-On.

The on-chip Flash enables a single-chip solution eliminating the need for external boot memory. This Flash can be programmed through either the JTAG or Slave SPI ports of the device. The SRAM configuration space can also be infinitely reconfigured through the JTAG and Master SPI ports. The JTAG port is IEEE 1149.1 and IEEE 1532 compliant.

As described in the EBR section of the data sheet, the FlashBAK capability of the parts enables the contents of the EBR blocks to be written back into the Flash storage area without erasing or reprogramming other aspects of the device configuration. Serial TAG memory is also available to allow the storage of small amounts of data such as calibration coefficients and error codes.

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM only FPGAs. This is further enhanced by device locking. The device can be in one of three modes:

original backup configuration and try again. This all can be done without power cycling the system. For more information please see TN1220, LatticeXP2 Dual Boot Feature.

For more information on device configuration, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Soft Error Detect (SED) Support

LatticeXP2 devices have dedicated logic to perform Cyclic Redundancy Code (CRC) checks. During configuration, the configuration data bitstream can be checked with the CRC logic block. In addition, LatticeXP2 devices can be programmed for checking soft errors in SRAM. SED can be run on a programmed device when the user logic is not active. In the event a soft error occurs, the device can be programmed to either reload from a known good boot image (from internal Flash or external SPI memory) or generate an error signal.

For further information on SED support, please see TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide.

On-Chip Oscillator

Every LatticeXP2 device has an internal CMOS oscillator that is used to derive a Master Clock (CCLK) for configuration. The oscillator and CCLK run continuously and are available to user logic after configuration is complete. The available CCLK frequencies are listed in Table 2-14. When a different CCLK frequency is selected during the design process, the following sequence takes place:

1. Device powers up with the default CCLK frequency.
2. During configuration, users select a different CCLK frequency.
3. CCLK frequency changes to the selected frequency after clock configuration bits are received.

This internal CMOS oscillator is available to the user by routing it as an input clock to the clock tree. For further information on the use of this oscillator for configuration or user mode, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

Table 2-14. Selectable CCLKs and Oscillator Frequencies During Configuration and User Mode

CCLK/Oscillator (MHz)
2.5[1]
3.1[2]
4.3
5.4
6.9
8.1
9.2
10
13
15
20
26
32
40
54
80[3]
163[3]

1. Software default oscillator frequency.
2. Software default CCLK frequency.
3. Frequency not valid for CCLK.

LVPECL

The LatticeXP2 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL

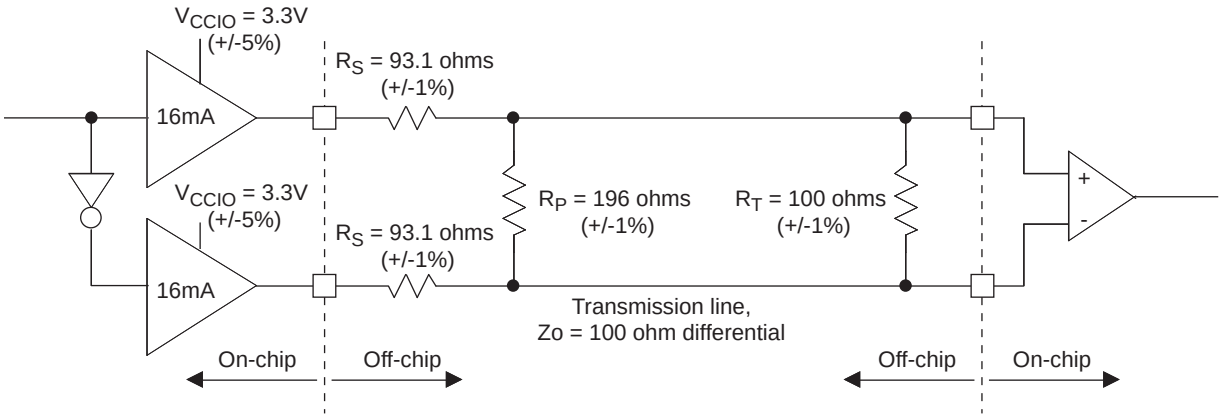


Table 3-3. LVPECL DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/-1%)	93	Ω
R_P	Driver Parallel Resistor (+/-1%)	196	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage (After R_P)	2.05	V
V_{OL}	Output Low Voltage (After R_P)	1.25	V
V_{OD}	Output Differential Voltage (After R_P)	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

RSDS

The LatticeXP2 devices support differential RSDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS (Reduced Swing Differential Standard)

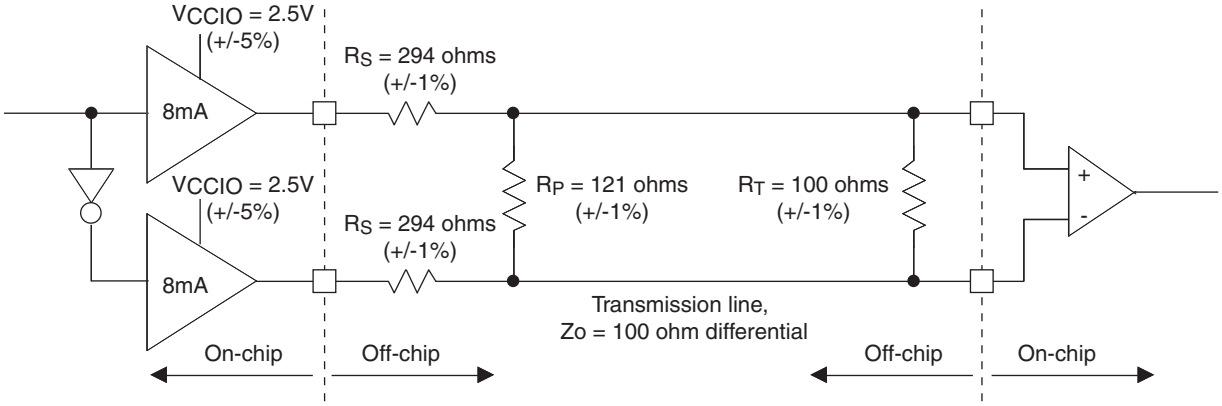


Table 3-4. RSDS DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (+/-1%)	294	Ω
R_P	Driver Parallel Resistor (+/-1%)	121	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage (After R_P)	1.35	V
V_{OL}	Output Low Voltage (After R_P)	1.15	V
V_{OD}	Output Differential Voltage (After R_P)	0.20	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	101.5	Ω
I_{DC}	DC Output Current	3.66	mA

1. For input buffer, see LVDS table.

LatticeXP2 External Switching Characteristics (Continued)

Over Recommended Operating Conditions

Parameter	Description	Device	-7		-6		-5		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{HE}	Clock to Data Hold - PIO Input Register	XP2-5	1.00	—	1.30	—	1.60	—	ns
		XP2-8	1.00	—	1.30	—	1.60	—	ns
		XP2-17	1.00	—	1.30	—	1.60	—	ns
		XP2-30	1.20	—	1.60	—	1.90	—	ns
		XP2-40	1.20	—	1.60	—	1.90	—	ns
t_{SU_DELE}	Clock to Data Setup - PIO Input Register with Data Input Delay	XP2-5	1.00	—	1.30	—	1.60	—	ns
		XP2-8	1.00	—	1.30	—	1.60	—	ns
		XP2-17	1.00	—	1.30	—	1.60	—	ns
		XP2-30	1.20	—	1.60	—	1.90	—	ns
		XP2-40	1.20	—	1.60	—	1.90	—	ns
t_{H_DELE}	Clock to Data Hold - PIO Input Register with Input Data Delay	XP2-5	0.00	—	0.00	—	0.00	—	ns
		XP2-8	0.00	—	0.00	—	0.00	—	ns
		XP2-17	0.00	—	0.00	—	0.00	—	ns
		XP2-30	0.00	—	0.00	—	0.00	—	ns
		XP2-40	0.00	—	0.00	—	0.00	—	ns
f_{MAX_IOE}	Clock Frequency of I/O and PFU Register	XP2	—	420	—	357	—	311	MHz
General I/O Pin Parameters (using Primary Clock with PLL)[1]									
t_{COPLL}	Clock to Output - PIO Output Register	XP2-5	—	3.00	—	3.30	—	3.70	ns
		XP2-8	—	3.00	—	3.30	—	3.70	ns
		XP2-17	—	3.00	—	3.30	—	3.70	ns
		XP2-30	—	3.00	—	3.30	—	3.70	ns
		XP2-40	—	3.00	—	3.30	—	3.70	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	XP2-5	1.00	—	1.20	—	1.40	—	ns
		XP2-8	1.00	—	1.20	—	1.40	—	ns
		XP2-17	1.00	—	1.20	—	1.40	—	ns
		XP2-30	1.00	—	1.20	—	1.40	—	ns
		XP2-40	1.00	—	1.20	—	1.40	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	XP2-5	0.90	—	1.10	—	1.30	—	ns
		XP2-8	0.90	—	1.10	—	1.30	—	ns
		XP2-17	0.90	—	1.10	—	1.30	—	ns
		XP2-30	1.00	—	1.20	—	1.40	—	ns
		XP2-40	1.00	—	1.20	—	1.40	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	XP2-5	1.90	—	2.10	—	2.30	—	ns
		XP2-8	1.90	—	2.10	—	2.30	—	ns
		XP2-17	1.90	—	2.10	—	2.30	—	ns
		XP2-30	2.00	—	2.20	—	2.40	—	ns
		XP2-40	2.00	—	2.20	—	2.40	—	ns

LatticeXP2 External Switching Characteristics (Continued)

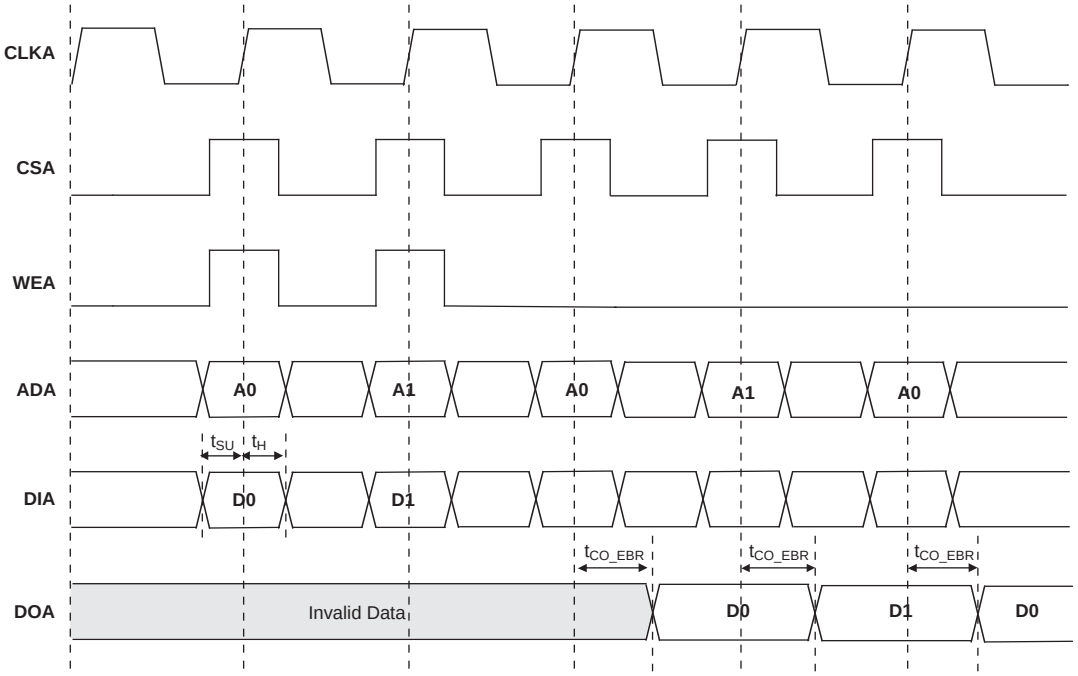
Over Recommended Operating Conditions

Parameter	Description	Device	-7		-6		-5		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	XP2-5	0.00	—	0.00	—	0.00	—	ns
		XP2-8	0.00	—	0.00	—	0.00	—	ns
		XP2-17	0.00	—	0.00	—	0.00	—	ns
		XP2-30	0.00	—	0.00	—	0.00	—	ns
		XP2-40	0.00	—	0.00	—	0.00	—	ns
DDR[2] and DDR2[3] I/O Pin Parameters									
t_{DVADQ}	Data Valid After DQS (DDR Read)	XP2	—	0.29	—	0.29	—	0.29	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	XP2	0.71	—	0.71	—	0.71	—	UI
t_{DQVBS}	Data Valid Before DQS	XP2	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	XP2	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR}	DDR Clock Frequency	XP2	95	200	95	166	95	133	MHz
f_{MAX_DDR2}	DDR Clock Frequency	XP2	133	200	133	200	133	166	MHz
Primary Clock									
f_{MAX_PRI}	Frequency for Primary Clock Tree	XP2	—	420	—	357	—	311	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	XP2	1	—	1	—	1	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Bank	XP2	—	160	—	160	—	160	ps
Edge Clock (ECLK1 and ECLK2)									
f_{MAX_ECLK}	Frequency for Edge Clock	XP2	—	420	—	357	—	311	MHz
t_{W_ECLK}	Clock Pulse Width for Edge Clock	XP2	1	—	1	—	1	—	ns
t_{SKEW_ECLK}	Edge Clock Skew Within an Edge of the Device	XP2	—	130	—	130	—	130	ps

1. General timing numbers based on LVCMOS 2.5, 12mA, 0pf load.
2. DDR timing numbers based on SSTL25.
3. DDR2 timing numbers based on SSTL18.

EBR Timing Diagrams

Figure 3-6. Read/Write Mode (Normal)



Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

Figure 3-7. Read/Write Mode with Input and Output Registers

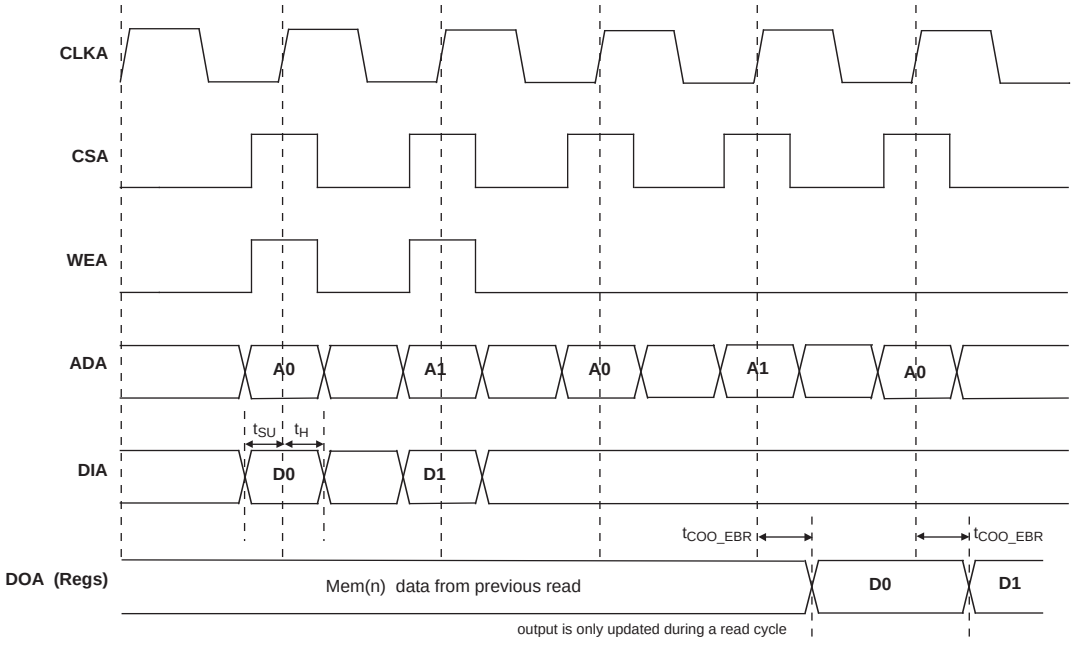
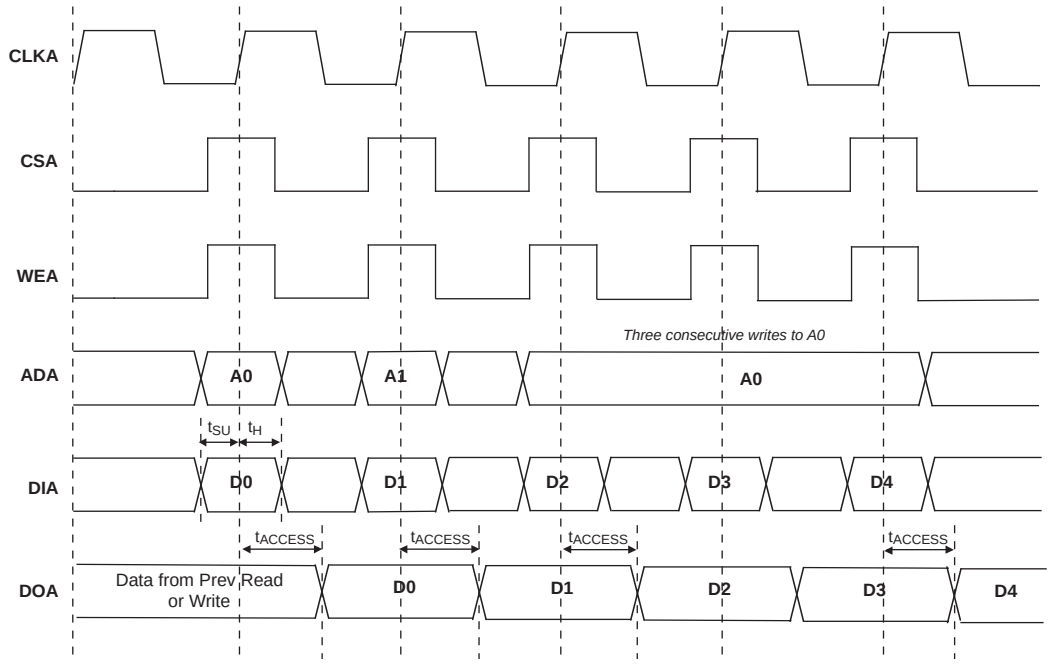


Figure 3-8. Write Through (SP Read/Write on Port A, Input Registers Only)



Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

LatticeXP2 Family Timing Adders[1, 2, 3, 4] (Continued)

Over Recommended Operating Conditions

Buffer Type	Description	-7	-6	-5	Units
HSTL15_I	HSTL_15 class I 4mA drive	0.32	0.69	1.06	ns
HSTL15D_I	Differential HSTL 15 class I 4mA drive	0.32	0.69	1.06	ns
SSTL33_I	SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33_II	SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL33D_I	Differential SSTL_3 class I	-0.25	0.05	0.35	ns
SSTL33D_II	Differential SSTL_3 class II	-0.31	-0.02	0.27	ns
SSTL25_I	SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25_II	SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL25D_I	Differential SSTL_2 class I 8mA drive	-0.25	0.02	0.30	ns
SSTL25D_II	Differential SSTL_2 class II 16mA drive	-0.28	0.00	0.28	ns
SSTL18_I	SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18_II	SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
SSTL18D_I	Differential SSTL_1.8 class I	-0.17	0.13	0.43	ns
SSTL18D_II	Differential SSTL_1.8 class II 8mA drive	-0.18	0.12	0.42	ns
LVTTL33_4mA	LVTTL 4mA drive	-0.37	-0.05	0.26	ns
LVTTL33_8mA	LVTTL 8mA drive	-0.45	-0.18	0.10	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.52	-0.24	0.04	ns
LVTTL33_16mA	LVTTL 16mA drive	-0.43	-0.14	0.14	ns
LVTTL33_20mA	LVTTL 20mA drive	-0.46	-0.18	0.09	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, fast slew rate	-0.37	-0.05	0.26	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, fast slew rate	-0.45	-0.18	0.10	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, fast slew rate	-0.52	-0.24	0.04	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, fast slew rate	-0.43	-0.14	0.14	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, fast slew rate	-0.46	-0.18	0.09	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, fast slew rate	-0.42	-0.15	0.13	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, fast slew rate	-0.48	-0.21	0.05	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, fast slew rate	-0.45	-0.18	0.08	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, fast slew rate	-0.49	-0.22	0.04	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, fast slew rate	-0.46	-0.18	0.10	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, fast slew rate	-0.52	-0.25	0.02	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, fast slew rate	-0.56	-0.30	-0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, fast slew rate	-0.50	-0.24	0.03	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, fast slew rate	-0.45	-0.17	0.11	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, fast slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, fast slew rate	-0.46	-0.19	0.08	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, fast slew rate	-0.55	-0.29	-0.02	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive, slow slew rate	0.98	1.41	1.84	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive, slow slew rate	0.74	1.16	1.58	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive, slow slew rate	0.56	0.97	1.38	ns
LVCMOS33_16mA	LVCMOS 3.3 16mA drive, slow slew rate	0.77	1.19	1.61	ns
LVCMOS33_20mA	LVCMOS 3.3 20mA drive, slow slew rate	0.57	0.98	1.40	ns

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Description	Conditions	Min.	Typ.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		10	—	435	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)		10	—	435	MHz
f_{OUT2}	K-Divider Output Frequency	CLKOK	0.078	—	217.5	MHz
		CLKOK2	3.3	—	145	MHz
f_{VCO}	PLL VCO Frequency		435	—	870	MHz
f_{PFD}	Phase Detector Input Frequency		10	—	435	MHz
AC Characteristics						
t_{DT}	Output Clock Duty Cycle	Default duty cycle selected [3]	45	50	55	%
t_{CPA}	Coarse Phase Adjust		-5	0	5	%
t_{PH} [4]	Output Phase Accuracy		-5	0	5	%
t_{OPJIT} [1]	Output Clock Period Jitter	f_{OUT} > 400 MHz	—	—	±50	ps
		100 MHz < f_{OUT} < 400 MHz	—	—	±125	ps
		f_{OUT} < 100 MHz	—	—	0.025	UIPP
t_{SK}	Input Clock to Output Clock Skew	N/M = integer	—	—	±240	ps
t_{OPW}	Output Clock Pulse Width	At 90% or 10%	1	—	—	ns
t_{LOCK} [2]	PLL Lock-in Time	25 to 435 MHz	—	—	50	µs
		10 to 25 MHz	—	—	100	µs
t_{IPJIT}	Input Clock Period Jitter		—	—	±200	ps
t_{FBKDLY}	External Feedback Delay		—	—	10	ns
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	—	ns
t_{RSTKW}	Reset Signal Pulse Width (RSTK)		10	—	—	ns
t_{RSTW}	Reset Signal Pulse Width (RST)		500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. Relative to CLKOP.

LatticeXP2 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description	Min	Max	Units
sysCONFIG POR, Initialization and Wake Up				
t_{ICFG}	Minimum Vcc to INITN High	—	50	ms
t_{VMC}	Time from t_{ICFG} to valid Master CCLK	—	2	µs
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection	—	12	ns
t_{PRGM}	PROGRAMN Low Time to Start Configuration	50	—	ns
t_{DINIT}[1]	PROGRAMN High to INITN High Delay	—	1	ms
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low	—	50	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low	—	50	ns
t_{IODISS}	User I/O Disable from PROGRAMN Low	—	35	ns
t_{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence	—	25	ns
t_{MWC}	Additional Wake Master Clock Signals after DONE Pin High	0	—	Cycles
sysCONFIG SPI Port (Master)				
t_{CFGX}	INITN High to CCLK Low	—	1	µs
t_{CSSPI}	INITN High to CSSPIN Low	—	2	µs
t_{CSCCLK}	CCLK Low before CSSPIN Low	0	—	ns
t_{SOCDO}	CCLK Low to Output Valid	—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First CCLK Edge Setup Time	2cyc	600+6cyc	ns
f_{MAXSPI}	Max CCLK Frequency	—	20	MHz
t_{SUSPI}	SOSPI Data Setup Time Before CCLK	7	—	ns
t_{HSPI}	SOSPI Data Hold Time After CCLK	10	—	ns
sysCONFIG SPI Port (Slave)				
$f_{MAXSPIS}$	Slave CCLK Frequency	—	25	MHz
t_{RF}	Rise and Fall Time	50	—	mV/ns
t_{STCO}	Falling Edge of CCLK to SOSPI Active	—	20	ns
t_{STOZ}	Falling Edge of CCLK to SOSPI Disable	—	20	ns
t_{STSU}	Data Setup Time (SISPI)	8	—	ns
t_{STH}	Data Hold Time (SISPI)	10	—	ns
t_{STCKH}	CCLK Clock Pulse Width, High	0.02	200	µs
t_{STCKL}	CCLK Clock Pulse Width, Low	0.02	200	µs
t_{STVO}	Falling Edge of CCLK to Valid SOSPI Output	—	20	ns
t_{SCS}	CSSPISN High Time	25	—	ns
t_{SCSS}	CSSPISN Setup Time	25	—	ns
t_{SCSH}	CSSPISN Hold Time	25	—	ns

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of PROGRAMN.

Lead-Free Packaging

Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	5
LFXP2-5E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	5
LFXP2-5E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	5
LFXP2-5E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	5
LFXP2-5E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	5
LFXP2-5E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	5
LFXP2-5E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	5
LFXP2-5E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	5
LFXP2-5E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	5
LFXP2-5E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	5
LFXP2-5E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	5
LFXP2-5E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	8
LFXP2-8E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	8
LFXP2-8E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	8
LFXP2-8E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	8
LFXP2-8E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	8
LFXP2-8E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	8
LFXP2-8E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	8
LFXP2-8E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	8
LFXP2-8E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	8
LFXP2-8E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	8
LFXP2-8E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	8
LFXP2-8E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	17
LFXP2-17E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	17
LFXP2-17E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	17
LFXP2-17E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	17
LFXP2-17E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	17
LFXP2-17E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	17
LFXP2-17E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	17
LFXP2-17E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	17
LFXP2-17E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208I	1.2V	-5	Lead-Free PQFP	208	IND	17
LFXP2-17E-6QN208I	1.2V	-6	Lead-Free PQFP	208	IND	17
LFXP2-17E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	17
LFXP2-17E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	17
LFXP2-17E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	17
LFXP2-17E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FTN256I	1.2V	-5	Lead-Free ftBGA	256	IND	30
LFXP2-30E-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	30
LFXP2-30E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	30
LFXP2-30E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	30
LFXP2-30E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	30
LFXP2-30E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5FN484I	1.2V	-5	Lead-Free fpBGA	484	IND	40
LFXP2-40E-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	40
LFXP2-40E-5FN672I	1.2V	-5	Lead-Free fpBGA	672	IND	40
LFXP2-40E-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	40

Conventional Packaging

Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5M132C	1.2V	-5	csBGA	132	COM	5
LFXP2-5E-6M132C	1.2V	-6	csBGA	132	COM	5
LFXP2-5E-7M132C	1.2V	-7	csBGA	132	COM	5
LFXP2-5E-5FT256C	1.2V	-5	ftBGA	256	COM	5
LFXP2-5E-6FT256C	1.2V	-6	ftBGA	256	COM	5
LFXP2-5E-7FT256C	1.2V	-7	ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5M132C	1.2V	-5	csBGA	132	COM	8
LFXP2-8E-6M132C	1.2V	-6	csBGA	132	COM	8
LFXP2-8E-7M132C	1.2V	-7	csBGA	132	COM	8
LFXP2-8E-5FT256C	1.2V	-5	ftBGA	256	COM	8
LFXP2-8E-6FT256C	1.2V	-6	ftBGA	256	COM	8
LFXP2-8E-7FT256C	1.2V	-7	ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5FT256C	1.2V	-5	ftBGA	256	COM	17
LFXP2-17E-6FT256C	1.2V	-6	ftBGA	256	COM	17
LFXP2-17E-7FT256C	1.2V	-7	ftBGA	256	COM	17
LFXP2-17E-5F484C	1.2V	-5	fpBGA	484	COM	17
LFXP2-17E-6F484C	1.2V	-6	fpBGA	484	COM	17
LFXP2-17E-7F484C	1.2V	-7	fpBGA	484	COM	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FT256C	1.2V	-5	ftBGA	256	COM	30
LFXP2-30E-6FT256C	1.2V	-6	ftBGA	256	COM	30
LFXP2-30E-7FT256C	1.2V	-7	ftBGA	256	COM	30
LFXP2-30E-5F484C	1.2V	-5	fpBGA	484	COM	30
LFXP2-30E-6F484C	1.2V	-6	fpBGA	484	COM	30
LFXP2-30E-7F484C	1.2V	-7	fpBGA	484	COM	30
LFXP2-30E-5F672C	1.2V	-5	fpBGA	672	COM	30
LFXP2-30E-6F672C	1.2V	-6	fpBGA	672	COM	30
LFXP2-30E-7F672C	1.2V	-7	fpBGA	672	COM	30

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5F484I	1.2V	-5	fpBGA	484	IND	40
LFXP2-40E-6F484I	1.2V	-6	fpBGA	484	IND	40
LFXP2-40E-5F672I	1.2V	-5	fpBGA	672	IND	40
LFXP2-40E-6F672I	1.2V	-6	fpBGA	672	IND	40

Date	Version	Section	Change Summary
April 2008 (cont.)	01.4 (cont.)	DC and Switching Characteristics (cont.)	Updated Flash Download Time (From On-Chip Flash to SRAM) Table
			Updated Flash Program Time Table
			Updated Flash Erase Time Table
			Updated FlashBAK (from EBR to Flash) Table
			Updated Hot Socketing Specifications Table footnotes
		Pinout Information	Updated Signal Descriptions Table
June 2008	01.5	Architecture	Removed Read-Before-Write sysMEM EBR mode.
			Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed Read-Before-Write sysMEM EBR mode.
		Pinout Information	Updated DDR Banks Bonding Out per I/O Bank section of Pin Information Summary Table.
August 2008	01.6	—	Data sheet status changed from preliminary to final.
		Architecture	Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed “8W” specification from Hot Socketing Specifications table.
			Removed "8W" footnote from DC Electrical Characteristics table.
			Updated Register-to-Register Performance table.
		Ordering Information	Removed “8W” option from Part Number Description.
			Removed XP2-17 “8W” OPNs.
April 2011	01.7	DC and Switching Characteristics	Recommended Operating Conditions table, added footnote 5.
			On-Chip Flash Memory Specifications table, added footnote 1.
			BLVDS DC Conditions, corrected column title to be Z0 = 90 ohms.
			sysCONFIG Port Timing Specifications table, added footnote 1 for t_{DINIT}.
January 2012	01.8	Multiple	Added support for Lattice Diamond design software.
		Architecture	Corrected information regarding SED support.
		DC and Switching Characteristics	Added reference to ESD Performance Qualification Summary information.
May 2013	01.9	All	Updated document with new corporate logo.
		Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			Added information regarding SED support.
		DC and Switching Characteristics	Removed Input Clock Rise/Fall Time 1ns max from the sysCLOCK PLL Timing table.
		Ordering Information	Updated topside mark in Ordering Information diagram.
March 2014	02.0	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Added information on POR signal deactivation.
August 2014	02.1	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Described user I/Os during power up and before FPGA core logic is active.
September 2014	2.2	DC and Switching Characteristics	Updated Switching Test Conditions section. Re-linked missing figure.